

UNISONIC TECHNOLOGIES CO., LTD

4N65K-TC Power MOSFET

4A, 650V N-CHANNEL **POWER MOSFET**

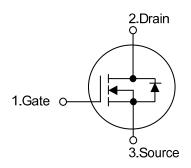
DESCRIPTION

The UTC 4N65K-TC is a high voltage power MOSFET designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and have a high rugged avalanche characteristic. This power MOSFET is usually used in high speed switching applications including power supplies, PWM motor controls, high efficient AC to DC converters and bridge circuits.

FEATURES

- * $R_{DS(ON)} \le 2.5\Omega$ @ V_{GS} =10V, I_D =2.0A
- * Fast Switching Capability
- * Avalanche Energy Specified
- * Improved dv/dt Capability, High Ruggedness

SYMBOL

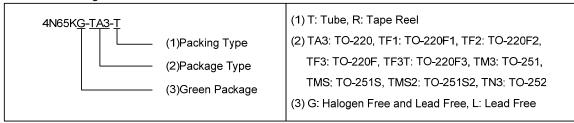


TO-220 TO-220F TO-220F1 TO-220F2 TO-220F3 TO-251 TO-251S2 TO-251S TO-252

ORDERING INFORMATION

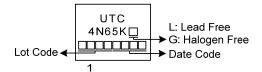
Ordering Number		Dookogo	Pin Assignment			Dooking	
Lead Free	Halogen Free	Package	1	2	3	Packing	
4N65KL-TA3-T	4N65KG-TA3-T	TO-220	G	D	S	Tube	
4N65KL-TF1-T	4N65KG-TF1-T	TO-220F1	G	D	S	Tube	
4N65KL-TF2-T	4N65KG-TF2-T	TO-220F2	G	D	S	Tube	
4N65KL-TF3-T	4N65KG-TF3-T	TO-220F	G	D	S	Tube	
4N65KL-TF3T-T	4N65KG-TF3T-T	TO-220F3	G	D	S	Tube	
4N65KL-TM3-T	4N65KG-TM3-T	TO-251	G	D	S	Tube	
4N65KL-TMS2-T	4N65KG-TMS2-T	TO-251S2	G	D	S	Tube	
4N65KL-TN3-R	4N65KG-TN3-R	TO-252	G	D	S	Tape Reel	

Note: Pin Assignment: G: Gate D: Drain S: Source



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■ MARKING



■ ABSOLUTE MAXIMUM RATINGS (T_C = 25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT	
Drain-Source Voltage		V_{DSS}	650	V	
Gate-Source Voltage		V_{GSS}	±30	V	
Drain Current	Continuous	I_{D}	4.0	Α	
	Pulsed (Note2)	I_{DM}	16	Α	
Avalanche Energy	Single Pulsed (Note3)	E_{AS}	113	mJ	
Peak Diode Recovery dv/dt (Note4)		dv/dt	3.79	V/ns	
Power Dissipation	TO-220		106	W	
	TO-220F/TO-220F1 TO-220F2/TO-220F3		36	W	
	TO-251/TO-251S TO-251S2/TO-252		50	W	
Derate above 25°C	TO-220	P_D	0.84	W/°C	
	TO-220F/TO-220F1 TO-220F2/TO-220F3		0.29	W/°C	
	TO-251/TO-251S TO-251S2/TO-252		0.40	W/°C	
Junction Temperature		T_J	+150	°C	
Operating Temperature		T _{OPR}	-55 ~ +150	°C	
Storage Temperature		T _{STG}	-55 ~ + 150	°C	

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

- 2. Repetitive Rating : Pulse width limited by maximum junction temperature
- 3. L=25mH, I_{AS} =3.0A, V_{DD} =50V, R_{G} =25 Ω , Starting T_{J} = 25°C
- 4. $I_{SD} \le 4.0A$, di/dt $\le 200A/\mu s$, $V_{DD} \le BV_{DSS}$, Starting $T_J = 25$ °C

■ THERMAL DATA

PARAMETER		SYMBOL	RATINGS	UNIT	
Junction to Ambient	TO-220/TO-220F TO-220F1/TO-220F2 TO-220F3	$ heta_{ extsf{JA}}$	62.5	°C/W	
	TO-251/TO-251S TO-251S2/TO-252		83	°C/W	
Junction to Case	TO-220		1.18	°C/W	
	TO-220F/TO-220F1 TO-220F3	0	3.4	°C/W	
	TO-220F2	$\theta_{ extsf{JC}}$	3.57	°C/W	
	TO-251/TO-251S TO-251S2/TO-252	2	2.5 (Note)	°C/W	

Note: The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.

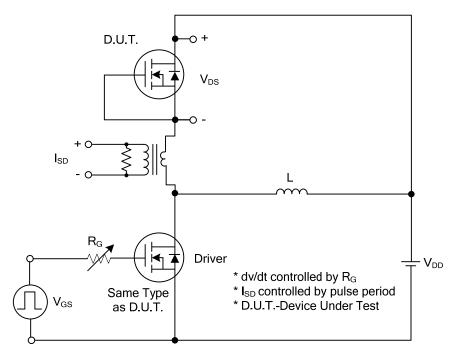
■ **ELECTRICAL CHARACTERISTICS** (T_C =25°C, unless otherwise specified)

PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
OFF CHARACTERISTICS								
Drain-Source Breakdown Voltage		BV _{DSS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	650			V	
Drain-Source Leakage Current		I _{DSS}	$V_{DS} = 650 \text{ V}, V_{GS} = 0 \text{ V}$			10	μA	
Gate-Source Leakage Current	Forward	GSS	$V_{GS} = 30 \text{ V}, V_{DS} = 0 \text{ V}$			100	nA	
	Reverse		$V_{GS} = -30 \text{ V}, V_{DS} = 0 \text{ V}$			-100	nA	
Breakdown Voltage Temperature Coefficient		$\triangle BV_{DSS}/\triangle T_{J}$	I _D =250μA, Referenced to 25°C		0.6		V/°C	
ON CHARACTERISTICS								
Gate Threshold Voltage		$V_{GS(TH)}$	$V_{DS} = V_{GS}$, $I_D = 250\mu A$			4.0	V	
Static Drain-Source On-State Res	istance	R _{DS(ON)}	V _{GS} = 10 V, I _D = 2.0A		2.2	2.5	Ω	
DYNAMIC CHARACTERISTICS								
Input Capacitance		C_{ISS}			600		pF	
Output Capacitance		Coss	V_{DS} =25V, V_{GS} =0V, f=1MHz		53.8		pF	
Reverse Transfer Capacitance	Reverse Transfer Capacitance				3.2		pF	
SWITCHING CHARACTERISTICS	S							
Total Gate Charge		Q_G	V _{DS} =100V, V _{GS} =10V, I _D =3.0A I _G = 1mA (Note1, 2)		13		nC	
Gate-Source Charge		Q_GS			3.6		nC	
Gate-Drain Charge		Q_GD	iig= iiiiA (Note i, 2)		2		nC	
Turn-On Delay Time		$t_{D(ON)}$			30		ns	
Turn-On Rise Time		t_R	V_{DS} =100V, V_{GS} =10V, I_{D} =2.0A,		10		ns	
Turn-Off Delay Time		$t_{D(OFF)}$	R _G =25Ω (Note1, 2)		60		ns	
Turn-Off Fall Time		t _F			50		ns	
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS								
Maximum Continuous Drain-Source Diode Forward Current		Is				4.0	Α	
						4.0	A	
Maximum Pulsed Drain-Source Diode		I _{SM}				16	Α	
Forward Current						10	^	
Drain-Source Diode Forward Voltage		V_{SD}	$V_{GS} = 0 \text{ V}, I_{S} = 4.0 \text{A}$			1.4	V	
Reverse Recovery Time		t _{rr}	V _{GS} = 0V, I _S = 4.0A,		230		nS	
Reverse Recovery Charge		Q_{rr}	dI _F / dt =100A/µs (Note 1)		1.6		μC	

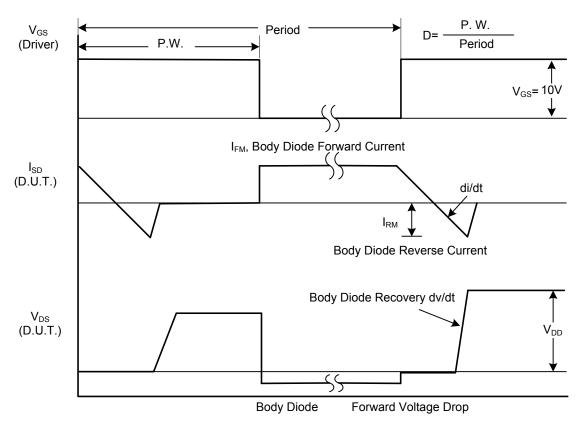
Notes: 1. Pulse Test: Pulse width ≤ 300µs, Duty cycle≤2%.

^{2.} Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS



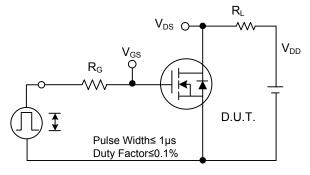
Peak Diode Recovery dv/dt Test Circuit



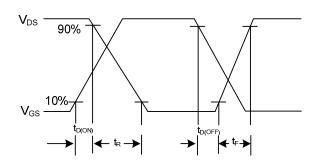
Peak Diode Recovery dv/dt Waveforms

4N65K-TC Power MOSFET

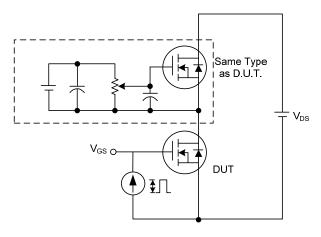
■ TEST CIRCUITS AND WAVEFORMS



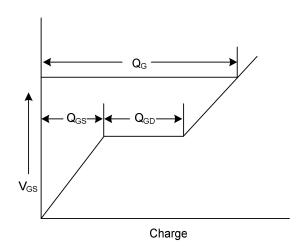
Switching Test Circuit



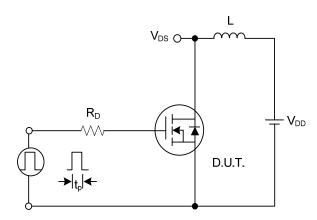
Switching Waveforms



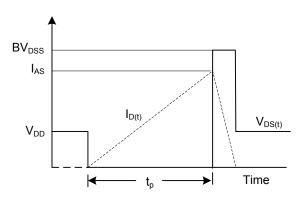
Gate Charge Test Circuit



Gate Charge Waveform

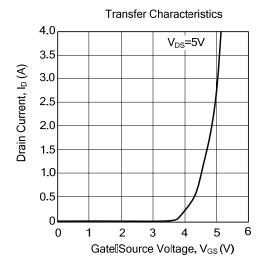


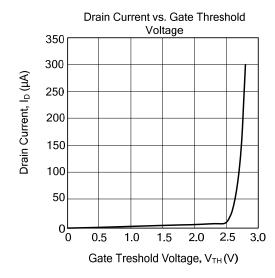
Unclamped Inductive Switching Test Circuit

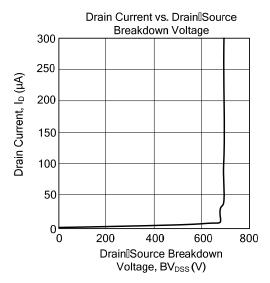


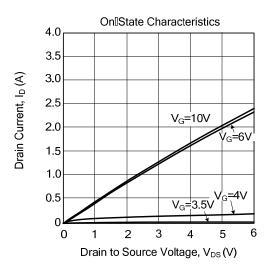
Unclamped Inductive Switching Waveforms

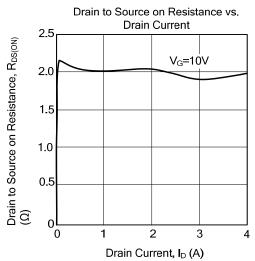
■ TYPICAL CHARACTERISTICS

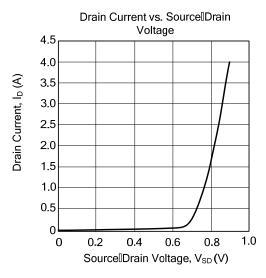




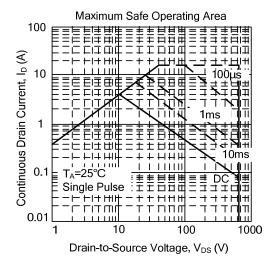








■ TYPICAL CHARACTERISTICS (Cont.)



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